ECH8309-TL-H Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	ECH8309-TL-H-DG
Manufacturer	onsemi
Manufacturer Product Number	ECH8309-TL-H
Description	MOSFET P-CH 12V 9.5A 8ECH
Detailed Description	P-Channel 12 V 9.5A (Ta) 1.5W (Ta) Surface Mount 8-ECH

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
ECH8309-TL-H	onsemi
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
12 V	9.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.8V, 4.5V	16mOhm @ 4.5A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
-	18 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±10V	1780 pF @ 6 V
FET Feature:	Power Dissipation (Max):
-	1.5W (Ta)
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
8-ECH	8-SMD, Flat Lead
Base Product Number:	
ECH8309	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

Ordering number : ENA1418B

ECH8309

P-Channel Power MOSFET
−12V, −9.5A, 16mΩ, Single ECH8

ON Semiconductor®
http://onsemi.com

Features

- 1.8V drive
- Halogen free compliance
- Protection diode in

Specifications

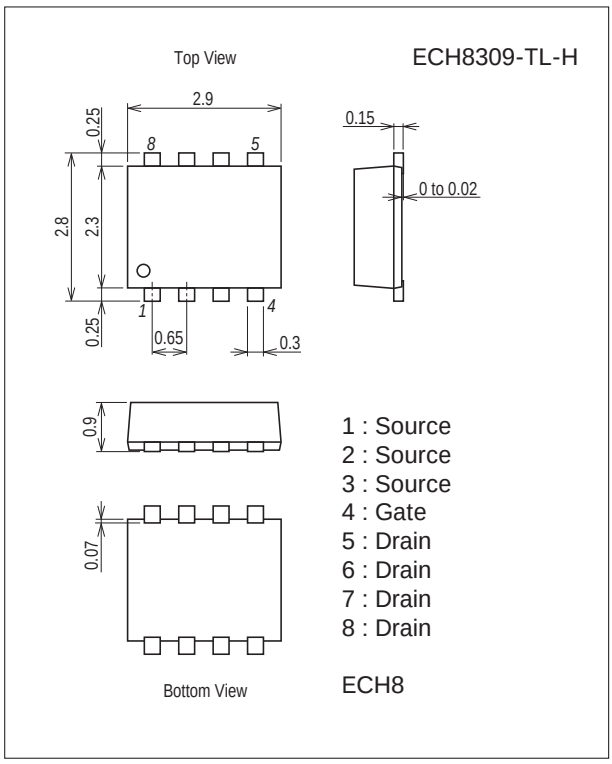
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		−12	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		−9.5	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−40	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

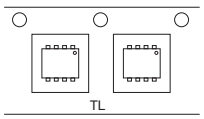
unit : mm (typ)
7011A-002



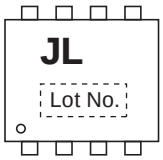
Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

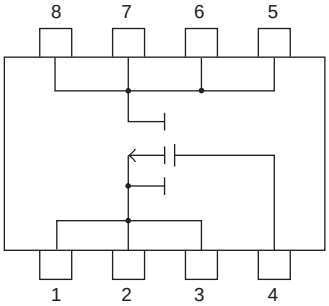
Packing Type : TL



Marking



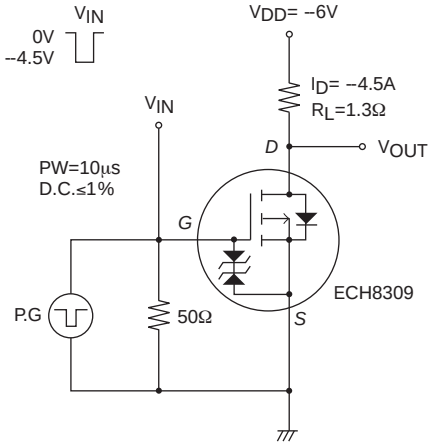
Electrical Connection



Electrical Characteristics at Ta=25°C

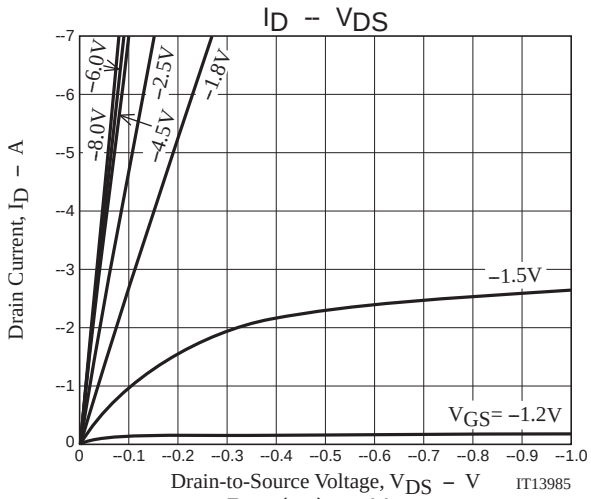
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−12			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−12V, V_{GS}=0V			−10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=−6V, I_D=−1mA	−0.4		−1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=−6V, I_D=−4.5A	9.6	16		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=−4.5A, V_{GS}=−4.5V		12	16	mΩ
	R_{DS}(on)2	I_D=−2A, V_{GS}=−2.5V		18	26	mΩ
	R_{DS}(on)3	I_D=−1A, V_{GS}=−1.8V		30	53	mΩ
Input Capacitance	Ciss	V_{DS}=−6V, f=1MHz		1780		pF
Output Capacitance	Coss			540		pF
Reverse Transfer Capacitance	Crss			390		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		22		ns
Rise Time	t_r			110		ns
Turn-OFF Delay Time	t_{d}(off)			157		ns
Fall Time	t_f			123		ns
Total Gate Charge	Qg	V_{DS}=−6V, V_{GS}=−4.5V, I_D=−9.5A		18		nC
Gate-to-Source Charge	Qgs			2.8		nC
Gate-to-Drain “Miller” Charge	Qgd			4.9		nC
Diode Forward Voltage	V_{SD}	I_S=−9.5A, V_{GS}=0V		−0.8	−1.2	V

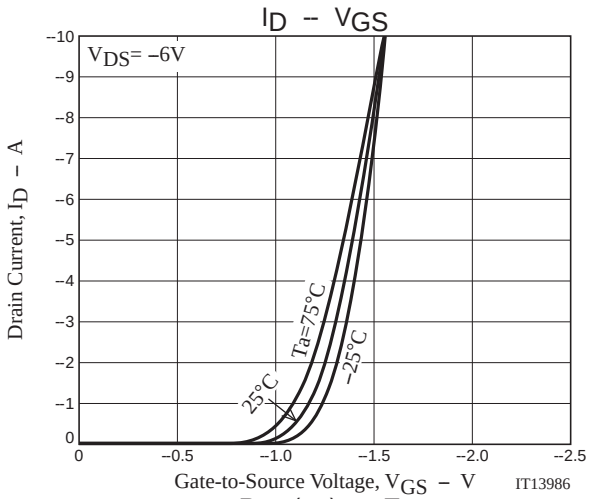
Switching Time Test Circuit

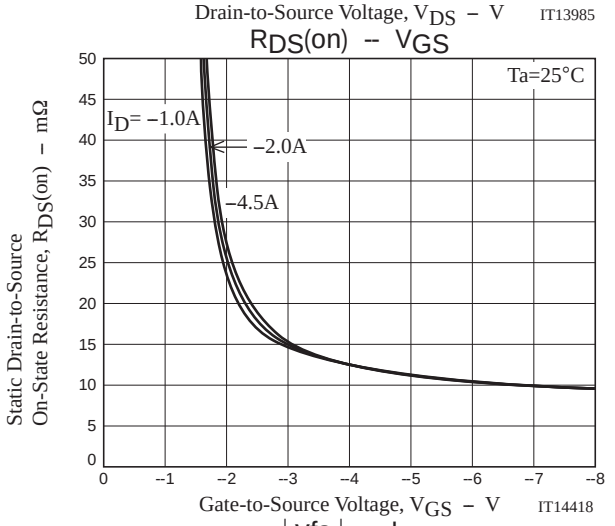


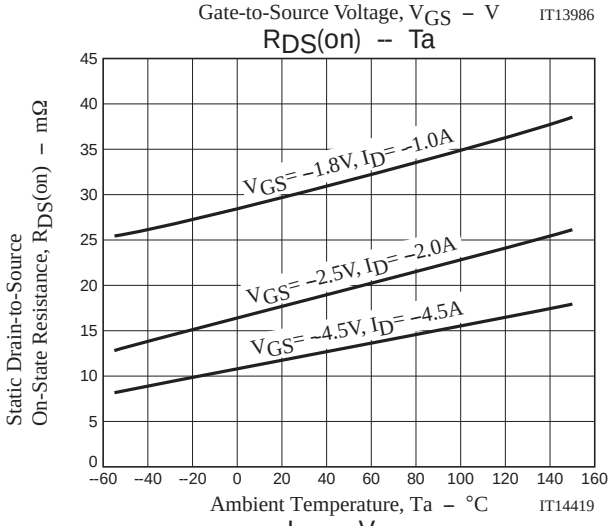
Ordering Information

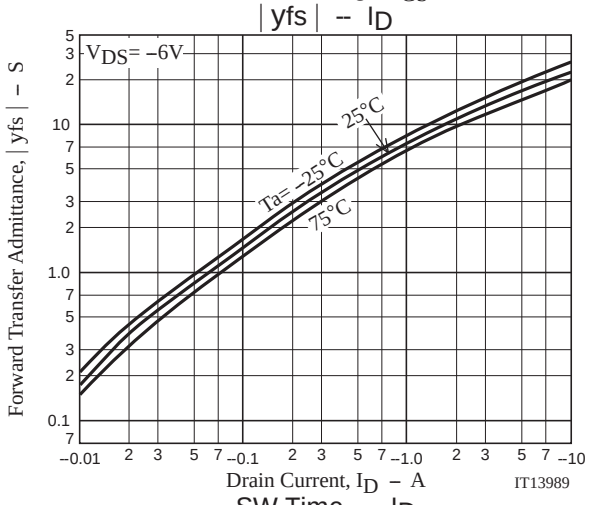
Device	Package	Shipping	memo
ECH8309-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free

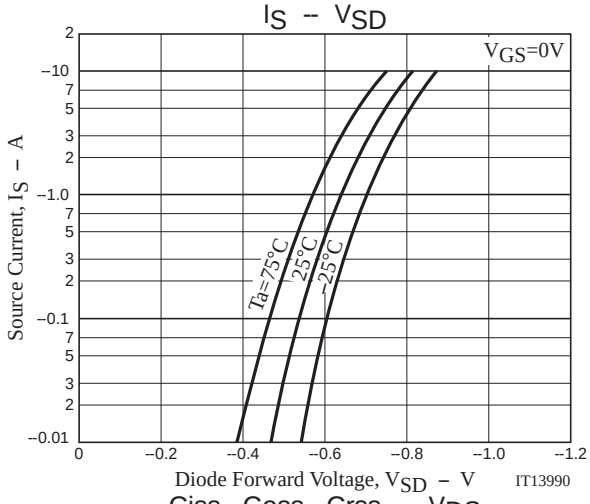

ID -- VDS
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT13985
–6.0V
–8.0V
–4.5V
–2.5V
–1.8V
–1.5V
VGS= –1.2V

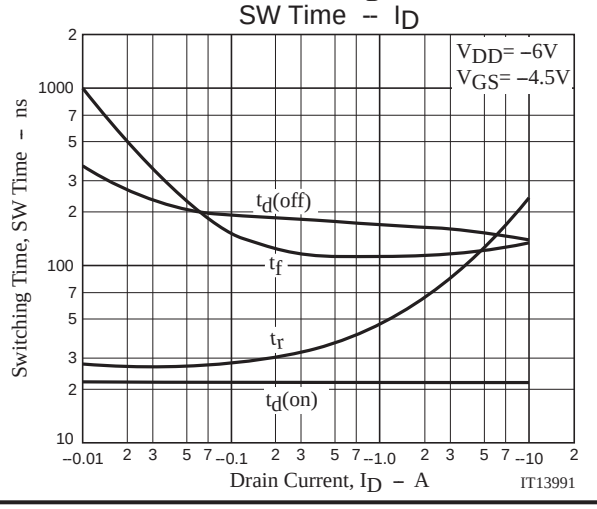

ID -- VGS
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
IT13986
VDS= –6V
Ta=75°C
25°C
–25°C

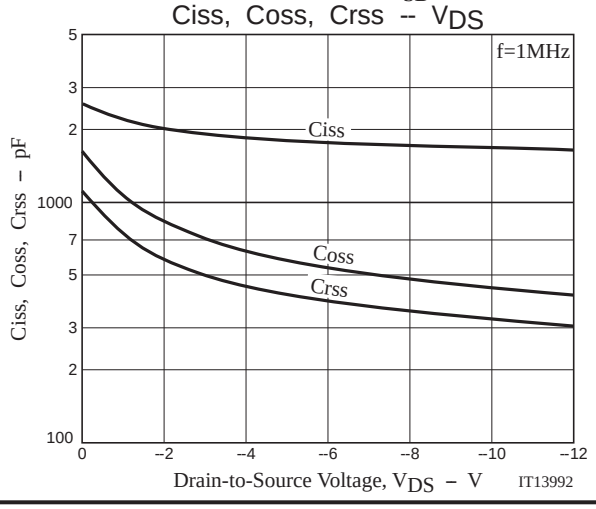

RDS(on) -- VGS
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT14418
Ta=25°C
ID= –1.0A
–2.0A
–4.5A

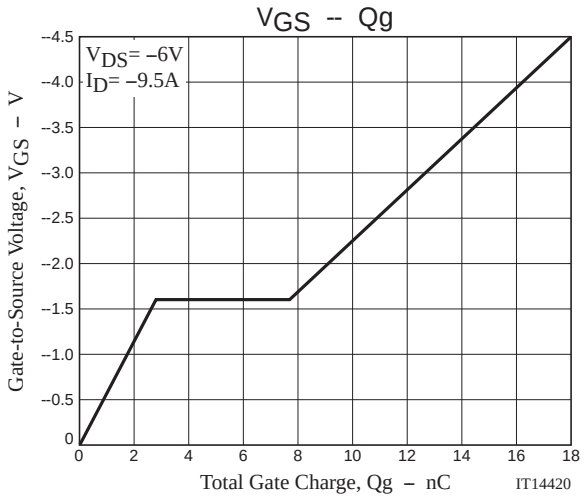

RDS(on) -- Ta
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT14419
VGS= –1.8V, ID= –1.0A
VGS= –2.5V, ID= –2.0A
VGS= –4.5V, ID= –4.5A

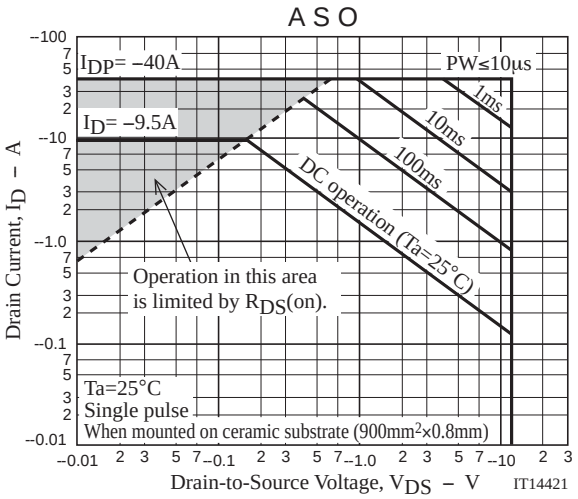

| yfs | -- ID
Forward Transfer Admittance, | yfs | – S
Drain Current, ID – A
IT13989
VDS= –6V
25°C
Ta= –25°C
75°C

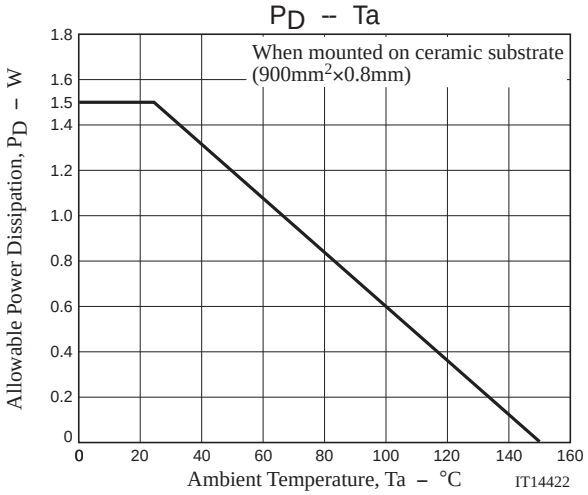

IS -- VSD
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT13990
VGS=0V
Ta=75°C
25°C
–25°C


SW Time -- ID
Switching Time, SW Time – ns
Drain Current, ID – A
IT13991
VDD= –6V
VGS= –4.5V
td(off)
tf
tr
td(on)


Ciss, Coss, Crss -- VDS
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT13992
f=1MHz
Ciss
Coss
Crss


VGS -- Qg
VDS= −6V
ID= −9.5A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT14420


A S O
IDP= −40A
PW≤10μs
ID= −9.5A
1ms
10ms
100ms
DC operation (Ta=25°C)
Operation in this area
is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate (900mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT14421


PD -- Ta
When mounted on ceramic substrate
(900mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT14422

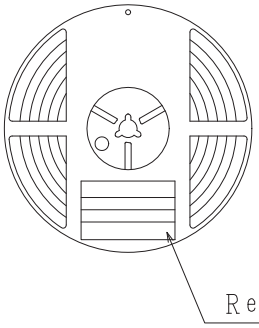
Embossed Taping Specification

ECH8309-TL-H

1. Packing Format

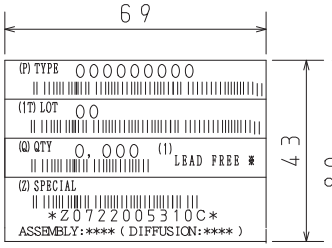
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



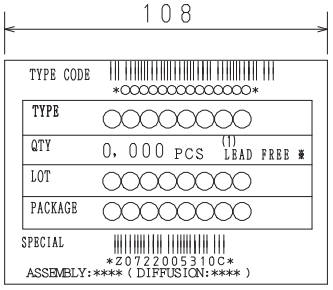
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



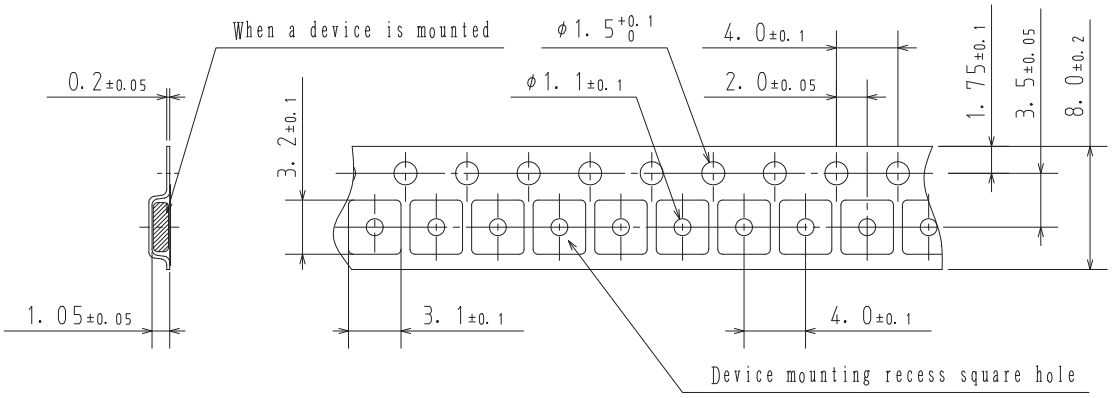
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

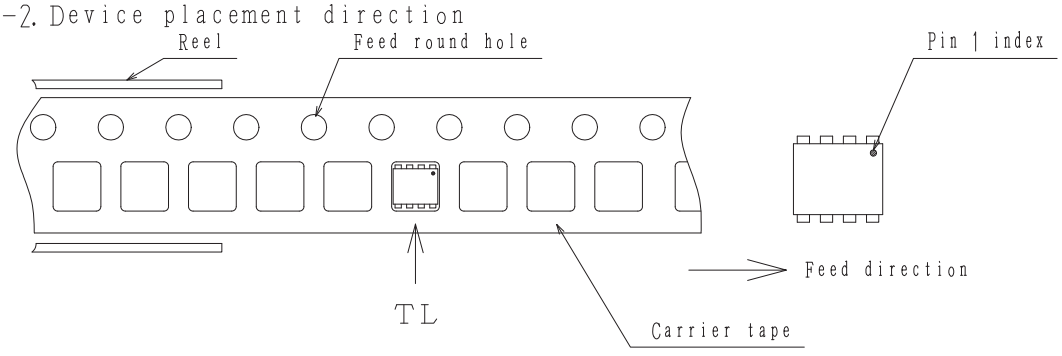
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

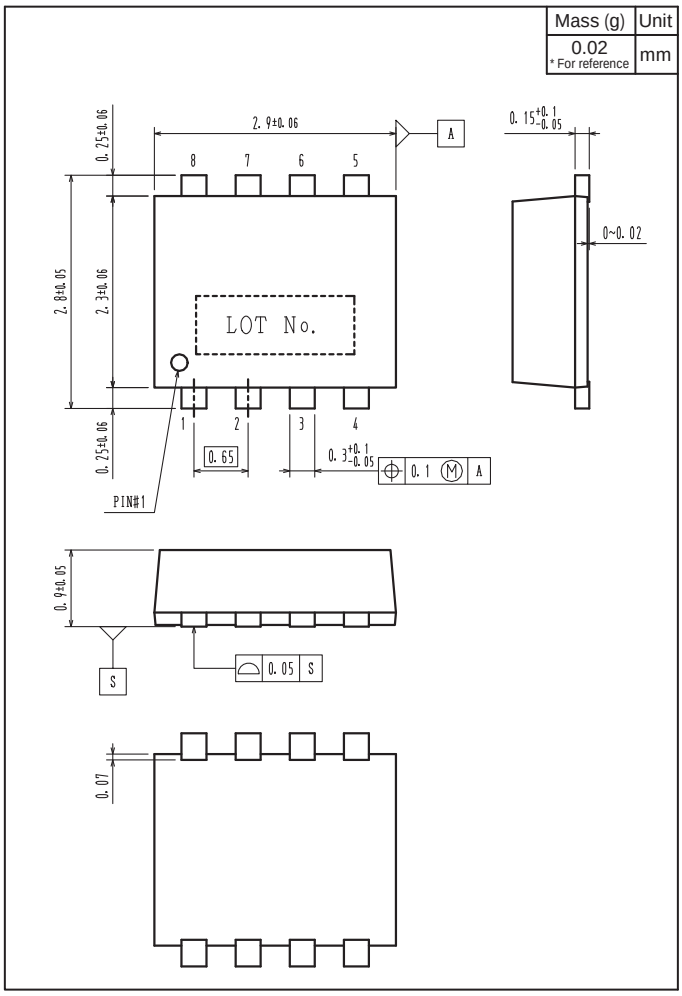


Those with pin 1 index on the feed hole side·····TL

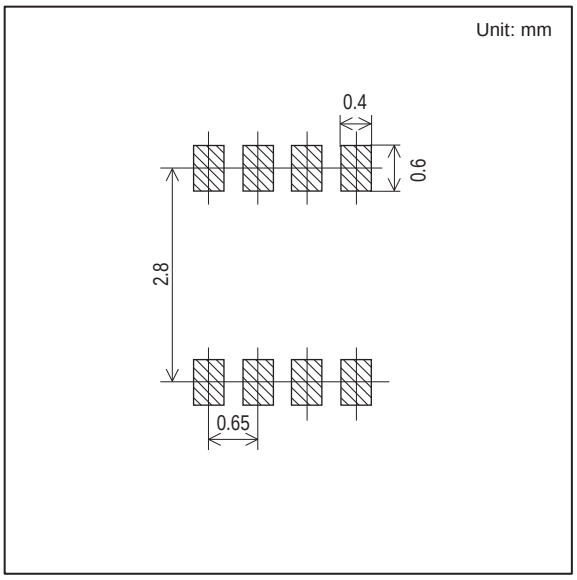
ECH8309

Outline Drawing

ECH8309-TL-H



Land Pattern Example



Note on usage : Since the ECH8309 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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